N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D (Silicon limited)	150A
$R_{DS(ON)}$(at V_{GS}=10V)	3.5 mohm
$R_{DS(ON)}$(at V_{GS}=4.5V)	5.0 mohm

100% EAS Tested
100% V_{DS} Tested
ESD Protected up to 2.0KV(HBM)

General Description

Split Gate Trench MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$

-0 Flammability Rating

alogen Free

Applications

Synchronous Rectification
Battery Protection Circuit
Motor drivers and Uninterruptible Power Supplies

Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	20	V
[redacted]	[redacted]	[redacted]	18	
Drain Current (Silicon limited)	T_A=100	I_D	11	A

Electrical Characteristics (T_j=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60,V_{GS}=0V			1	
		V_{DS}=60,V_{GS}=0V, Tj=150			100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= 20V, V_{DS}=0V			10	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= 10V, I_D=20A		2.7	3.5	m
		V_{GS}= 4.5V, I_D=20A		3.5	4.8	m
Diode Forward Voltage	V_{SD}	I_S=20A,V_{GS}=0V		0.8	1.3	V
Maximum Body-Diode Continuous Current	I_S				150	A
Gate resistance	R_G	f= 1 MHz		2.0		
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=30V,V_{GS}=0V,f=1MHZ		4650		pF
Output Capacitance	C_{oss}			850		
Reverse Transfer Capacitance	C_{rss}			65		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=30V,I_D=25A		71		nC
Gate-Source Charge	Q_{gs}			17		
Gate-Drain Charge	Q_{gd}			10.5		
Reverse Recovery Chrage	Q_{rr}	I_F=20A, di/dt=500A/us		39.8		
Reverse Recovery Time	t_{rr}			41.6		ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V,V_{DD}=30V,ID=25A R_{GEN}=2		15.9		
Turn-on Rise Time	t_r			55.2		
Turn-off Delay Time	$t_{D(off)}$			57.5		
Turn-off fall Time	t_f			91.3		

A. Repetitive rating; pulse width limited by max. junction temperature.
B. V_{DD}=50V, R_G 0.5mH, I_{AS}=42A.
C. Pd is based on max. junction temperature, using junction-case thermal resistance.
D. The value of R $_{JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25 C. The Power dissipation P_{DSM} is based on R $_{JA}$ tion temperature of 150 C. The value in any given application depends on the user's specific board design.

Typical Performance Characteristics

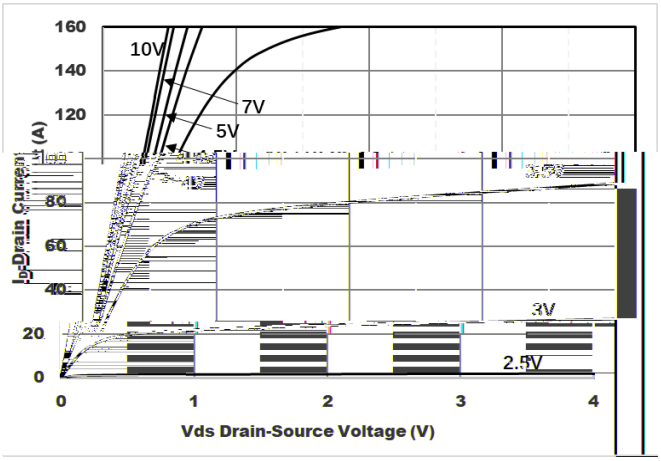


Figure1. Output Characteristics

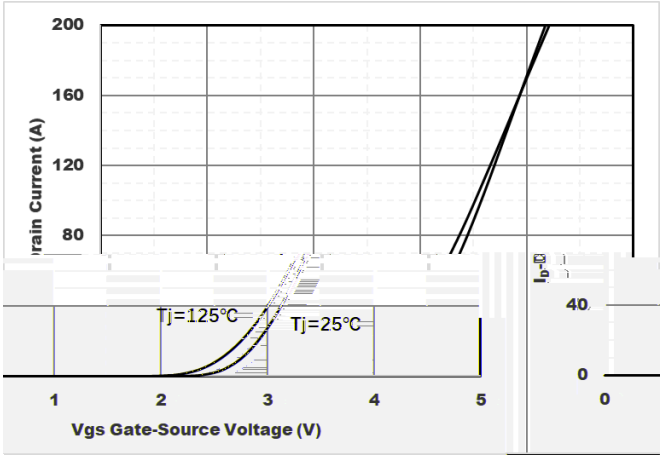


Figure2. Transfer Characteristics

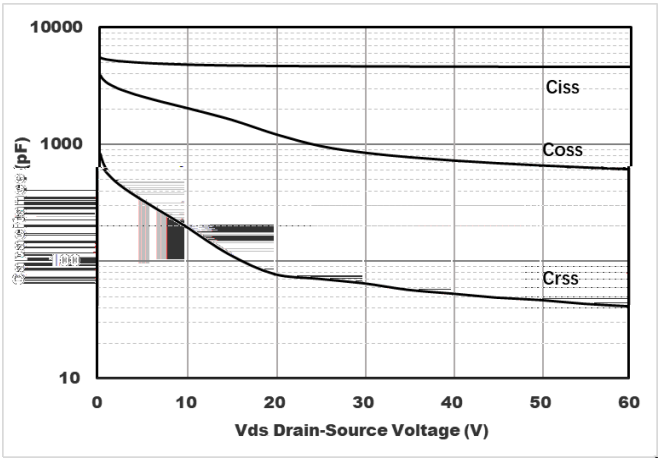


Figure3. Capacitance Characteristics

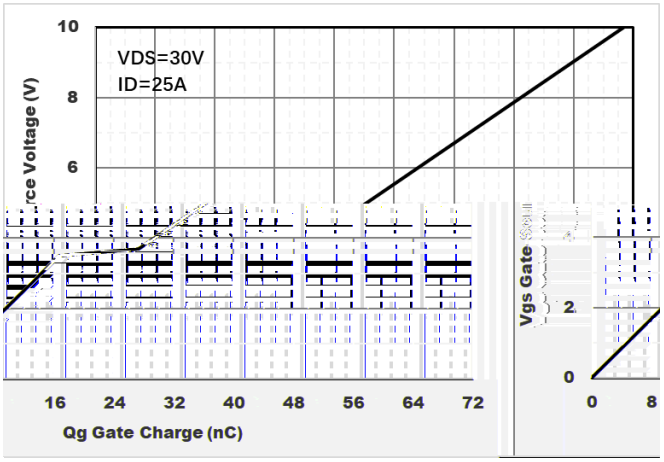


Figure4. Gate Charge

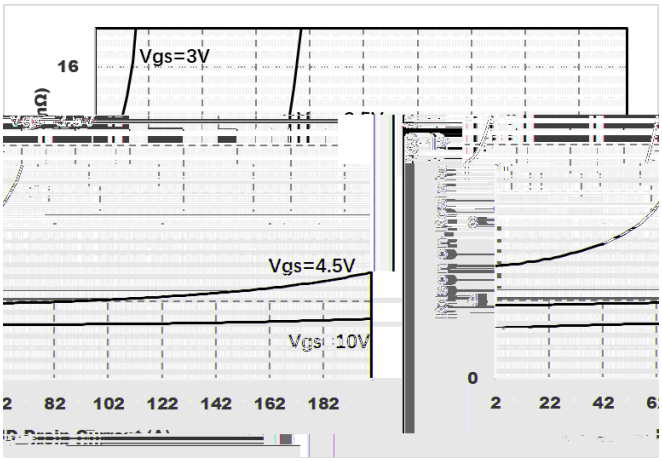


Figure5. On-Resistance vs. Drain Current and Gate Voltage

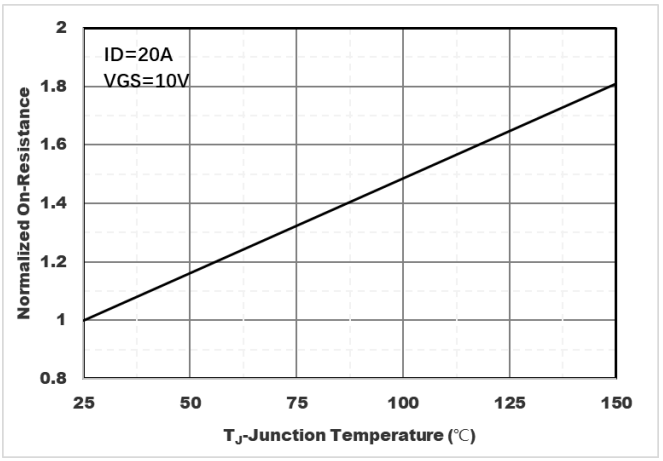


Figure6. Normalized On-Resistance

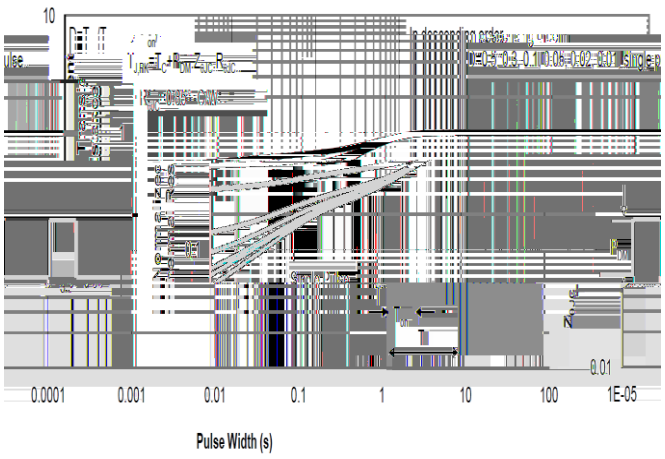


Figure13. Normalized Maximum Transient thermal impedance

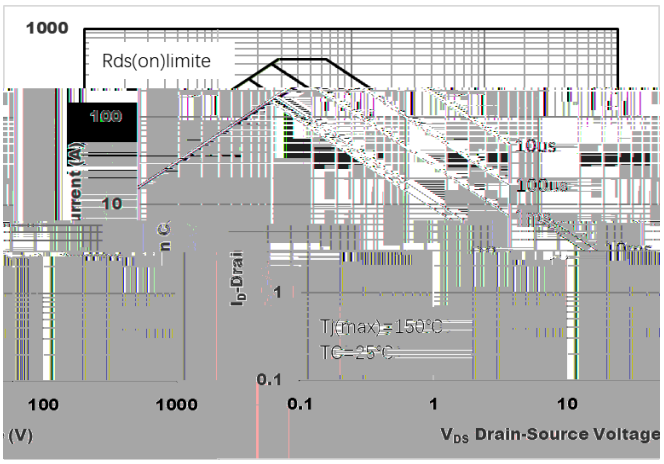
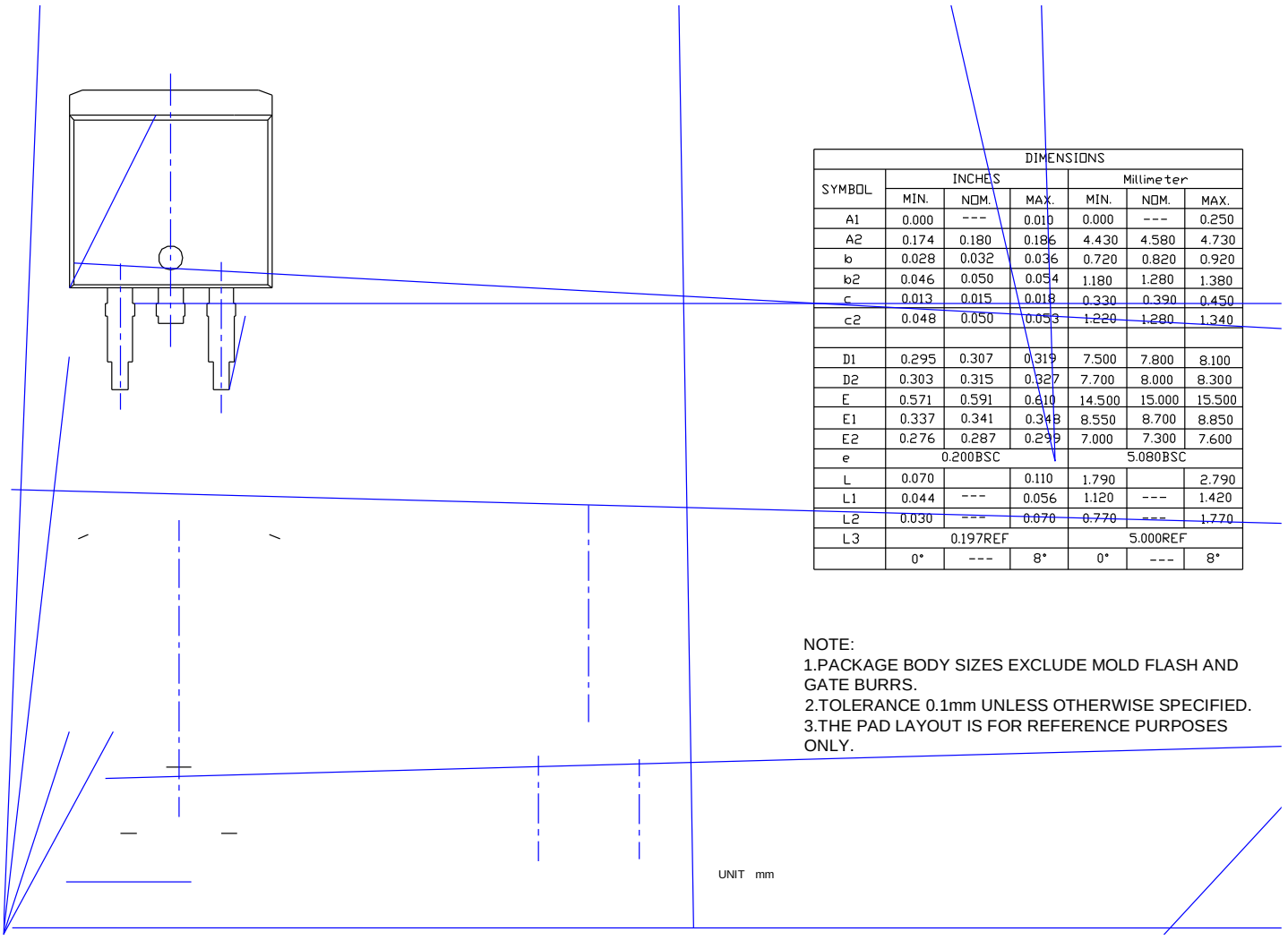


Figure14. Safe Operation Area

TO-263-HY Package information



DIMENSIONS						
SYMBOL	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.340
D1	0.295	0.307	0.319	7.500	7.800	8.100
D2	0.303	0.315	0.327	7.700	8.000	8.300
E	0.571	0.591	0.610	14.500	15.000	15.500
E1	0.337	0.341	0.348	8.550	8.700	8.850
E2	0.276	0.287	0.299	7.000	7.300	7.600
e	0.200BSC			5.080BSC		
L	0.070		0.110	1.790		2.790
L1	0.044	---	0.056	1.120	---	1.420
L2	0.030	---	0.070	0.770	---	1.770
L3	0.197REF			5.000REF		
	0°	---	8°	0°	---	8°

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

UNIT mm